Product data sheet

1. General description

The 74LV153 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC153 and 74HCT153.

The 74LV153 provides a dual 4-input multiplexer which selects 2 bits of data from up to four sources selected by common data select inputs (S0, S1). The two 4-input multiplexer circuits have individual active LOW output enable inputs (1E, 2E) which can be used to strobe the outputs independently. The outputs (1Y, 2Y) are forced LOW when the corresponding output enable inputs are HIGH. The 74LV153 is the logic implementation of a 2-pole, 4-position switch, where the position of the switch, is determined by the logic levels applied to S0 and S1. The logic equations for the outputs are:

 $1Y = 1\overline{E} \times (1I0 \times \overline{S1} \times \overline{S0} + 1I1 \times \overline{S1} \times S0 + 1I2 \times S1 \times \overline{S0} + 1I3 \times S1 \times S0)$ $2Y = 2\overline{E} \times (2I0 \times \overline{S1} \times \overline{S0} + 2I1 \times \overline{S1} \times S0 + 2I2 \times S1 \times \overline{S0} + 2I3 \times S1 \times S0)$

The 74LV153 can be used to move data to a common output bus from a group of registers. The state of the select inputs would determine the particular register from which the data came. An alternative application is a function generator. The device can generate two functions or three variables. This is useful for implementing highly irregular random logic.

2. Features and benefits

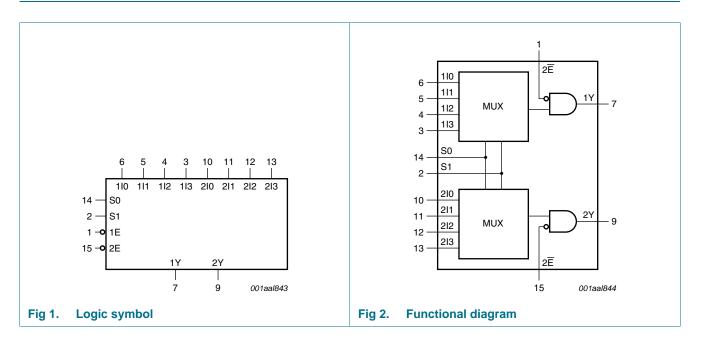
- Wide operating voltage: 1.0 V to 3.6 V
- Accepts TTL input levels between V_{CC} = 2.7 V and V_{CC} = 3.6 V
- Typical output ground bounce < 0.8 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at V_{CC} = 3.3 V and T_{amb} = 25 °C
- Non-inverting outputs
- Separate enable input for each output
- Common select inputs
- Permits multiplexing from n lines to 1 line
- Enable line provided for cascading (n lines to 1 line)
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

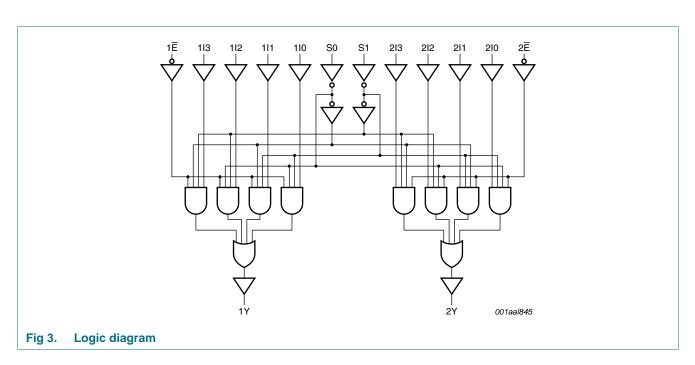


3. Ordering information

Table 1. Ordering information								
Type number	Package							
	Temperature range	Name	Description	Version				
74LV153N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4				
74LV153D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1				
74LV153DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1				
74LV153PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1				

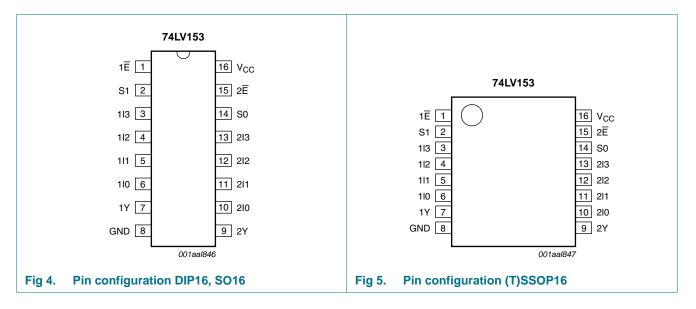
4. Functional diagram





5. Pinning information

5.1 Pinning



74LV153_4 Product data sheet

74LV153

Dual 4-input multiplexer

5.2 Pin description

Symbol	Pin	Description
1Ē, 2Ē	1, 15	output enable inputs (active LOW)
S0, S1	14, 2	data select inputs
110, 111, 112, 113	6, 5, 4, 3	data inputs source 1
1Y	7	multiplexer output source 1
GND	8	ground (0 V)
2Y	9	multiplexer output source 2
210, 211, 212, 213	10, 11, 12, 13	data inputs source 2
V _{CC}	16	supply voltage

6. Functional description

Table 3.Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care.

select Inputs		data inpu	data inputs				output	
S0	S1	nl0	nl1	nl2	nl3	nE	nY	
Х	Х	Х	Х	Х	Х	Н	L	
L	L	L	Х	Х	Х	L	L	
L	L	Н	Х	Х	Х	L	Н	
Н	L	Х	L	Х	Х	L	L	
Н	L	Х	Н	Х	Х	L	Н	
L	Н	Х	Х	L	Х	L	L	
L	Н	Х	Х	Н	Х	L	Н	
Н	Н	Х	Х	Х	L	L	L	
Н	Н	Х	Х	Х	Н	L	Н	

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	V_{O} < -0.5 V or V_{O} > V_{CC} + 0.5 V	<u>[1]</u> _	±50	mA
I _O	output current	$V_{O} = -0.5 \text{ V}$ to (V_{CC} + 0.5 V)	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$			
	DIP16 package		[2] _	750	mW
	SO16 package		<u>[3]</u> _	500	mW
	(T)SSOP16 package		<u>[4]</u> _	500	mW

Table 4. Limiting values ... continued

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

P_{tot} derates linearly with 12 mW/K above 70 °C. [2]

 P_{tot} derates linearly with 8 mW/K above 70 $^\circ\text{C}.$ [3]

 P_{tot} derates linearly with 5.5 mW/K above 60 $^\circ\text{C}.$ [4]

Recommended operating conditions 8.

Table 5. **Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

•		,				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		^[1] 1.0	3.3	3.6	V
VI	input voltage		0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	V_{CC} = 1.0 V to 2.0 V	-	-	500	ns/V
		V_{CC} = 2.0 V to 2.7 V	-	-	200	ns/V
		V_{CC} = 2.7 V to 3.6 V	-	-	100	ns/V

[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V, but LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

Table 6.

Dual 4-input multiplexer

9. Static characteristics

Static characteristics

	are referenced to GND (grou							
Symbol	Parameter	Conditions	-40	°C to +8	5 °C	–40 °C to +125 °C		Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	0.9	-	-	0.9	-	V
		$V_{CC} = 2.0 V$	1.4	-	-	1.4	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.3	-	0.3	V
		$V_{CC} = 2.0 V$	-	-	0.6	-	0.6	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$						
		I_{O} = –100 $\mu A;$ V_{CC} = 1.2 V	-	1.2	-	-	-	V
		I_{O} = –100 $\mu A;$ V_{CC} = 2.0 V	1.8	2.0	-	1.8	-	V
		I_{O} = –100 $\mu A;$ V_{CC} = 2.7 V	2.5	2.7	-	2.5	-	V
		I_{O} = –100 $\mu A;$ V_{CC} = 3.0 V	2.8	3.0	-	2.8	-	V
		$I_O = -6$ mA; $V_{CC} = 3.0$ V	2.4	2.82	-	2.2	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$						
		I_O = 100 μ A; V_{CC} = 1.2 V	-	0	-	-	-	V
		I_O = 100 μ A; V_{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I_{O} = 100 $\mu\text{A};V_{CC}$ = 2.7 V	-	0	0.2	-	0.2	V
		I_O = 100 μ A; V_{CC} = 3.0 V	-	0	0.2	-	0.2	V
		$I_{O} = 6 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.25	0.40	-	0.50	V
l _l	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 3.6 V$	-	-	1.0	-	1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 3.6$ V	-	-	20.0	-	160	μΑ
∆l _{CC}	additional supply current	per input; V _I = V _{CC} – 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	μΑ
CI	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; For test circuit see Figure 8.

Symbol	Parameter	Conditions		-40	°C to +85	5 °C	−40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	1In to 1Y and 2In to 2Y; see <u>Figure 6</u>	[2]						
		V _{CC} = 1.2 V		-	85	-	-	-	ns
		$V_{CC} = 2.0 V$		-	29	56	-	66	ns
		$V_{CC} = 2.7 V$		-	21	41	-	49	ns
		V_{CC} = 3.3 V; C_{L} = 15 pF		-	14	-	-	-	ns
		V_{CC} = 3.0 V to 3.6 V	<u>[3]</u>	-	16	33	-	39	ns
		Sn to nY; see Figure 6							
		$V_{CC} = 1.2 V$		-	90	-	-	-	ns
		$V_{CC} = 2.0 V$		-	31	58	-	70	ns
		$V_{CC} = 2.7 V$		-	23	43	-	51	ns
		V_{CC} = 3.3 V; C_{L} = 15 pF		-	14	-	-	-	ns
		V_{CC} = 3.0 V to 3.6 V	[3]	-	17	34	-	41	ns
		nE to nY; see Figure 6							
		$V_{CC} = 1.2 V$		-	60	-	-	-	ns
		$V_{CC} = 2.0 V$		-	20	39	-	46	ns
		$V_{CC} = 2.7 V$		-	15	29	-	34	ns
		V_{CC} = 3.3 V; C_{L} = 15 pF		-	10	-	-	-	ns
		V_{CC} = 3.0 V to 3.6 V	<u>[3]</u>	-	11	23	-	27	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	<u>[4]</u>	-	30	-	-	-	pF

[1] All typical values are measured at $T_{amb} = 25 \text{ °C}$.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V) unless otherwise stated.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 $f_i = \text{input}$ frequency in MHz, $f_o = \text{output}$ frequency in MHz

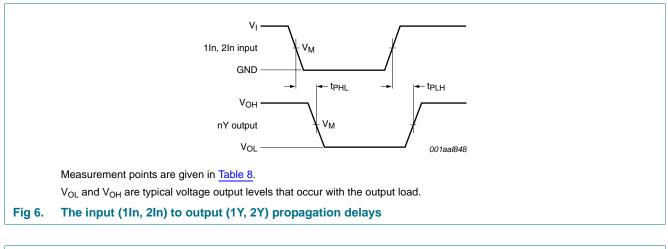
 C_L = output load capacitance in pF

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

 V_{CC} = supply voltage in V

11. Waveforms



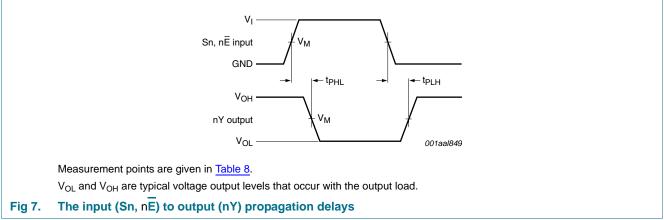


Table 8. Measurement points

Supply voltage	Input	Output
V _{cc}	V _M	V _M
< 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V to 3.6 V	1.5 V	1.5 V

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74LV153

Dual 4-input multiplexer

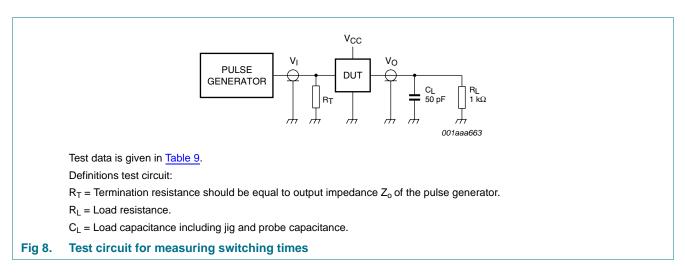


Table 9. Test data

Supply voltage	Input	
V _{cc}	VI	t _r , t _f
< 2.7 V	V _{CC}	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns

12. Package outline

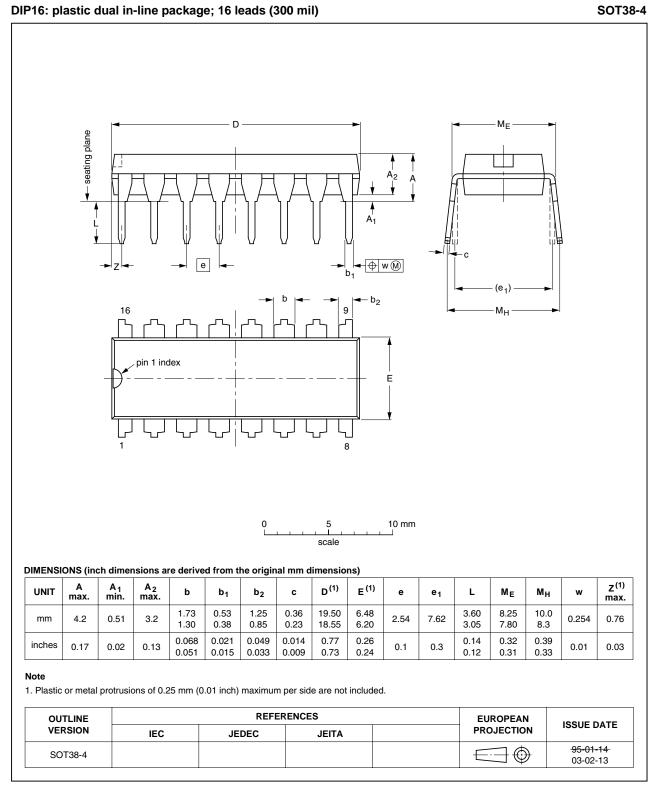
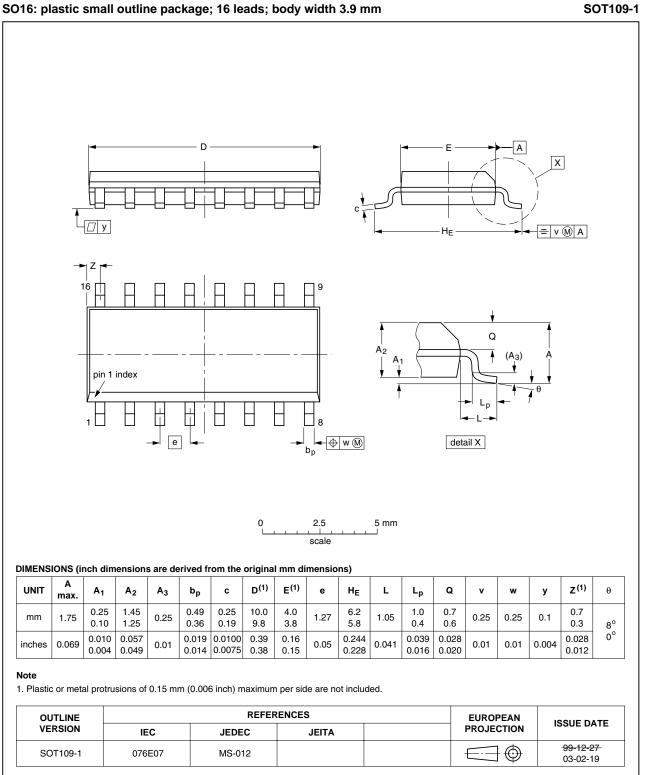


Fig 9. Package outline SOT38-4 (DIP16)

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SO16: plastic small outline package; 16 leads; body width 3.9 mm

Fig 10. Package outline SOT109-1 (SO16)

74LV153_4 **Product data sheet**

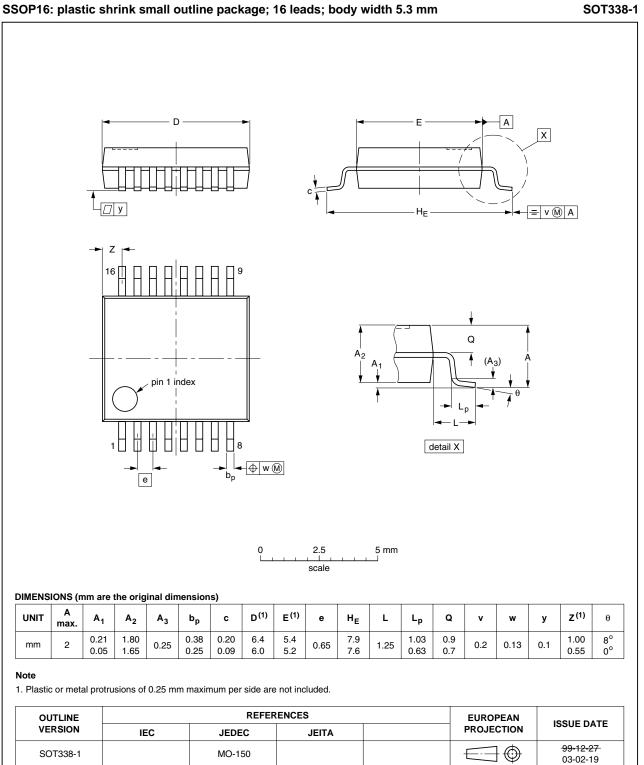


Fig 11. Package outline SOT338-1 (SSOP16)

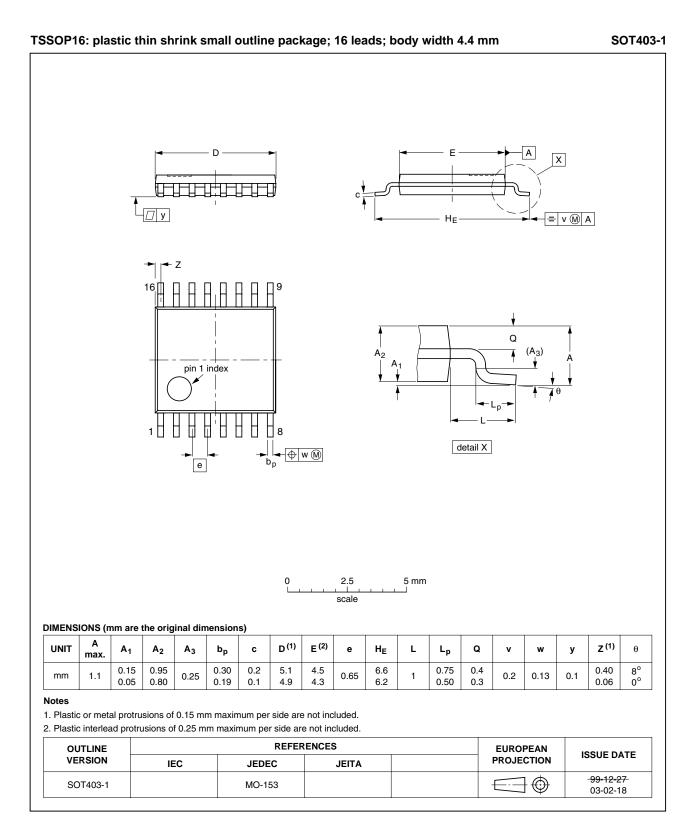


Fig 12. Package outline SOT403-1 (TSSOP16)

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13. Abbreviations

Table 10. Abbreviations						
Acronym	Description					
CMOS	Complementary Metal Oxide Semiconductor					
DUT	Device Under Test					
ESD	ElectroStatic Discharge					
HBM	Human Body Model					
MM	Machine Model					
TTL	Transistor-Transistor Logic					

14. Revision history

Table 11. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
74LV153_4	20100429	Product data sheet	-	74LV153_3		
Modifications: • The format of this data sheet has been redesigned to comply with the new identity guide of NXP Semiconductors.						
	 Legal texts have 	ve been adapted to the new	company name where	appropriate.		
74LV153_3	19980428	Product specification	-	74LV153_2		
74LV153_2	19970515	Product specification	-	-		

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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